

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims:

1. (currently amended): A semiconductor device comprising:
 - a first insulating film formed over a semiconductor substrate;
 - a capacitor constructed by forming a lower electrode, a dielectric film, and an upper electrode sequentially over the first insulating film;
 - a first capacitor protection insulating film covering the dielectric film and the upper electrode;
 - a second capacitor protection insulating film formed on the first capacitor protection insulating film; and
 - a second insulating film formed on the second capacitor protection insulating film; wherein an amount of carbon contained in the second capacitor protection insulating film is larger than an amount of carbon contained in the second insulating film,
wherein the second capacitor protection insulating film is a silicon oxide film, and
wherein the second insulating film is a silicon oxide film.

2.-3. (canceled)

4. (original): A semiconductor device according to claim 1, wherein the first capacitor protection insulating film is made of any one of alumina, PLZT, PZT, titanium oxide, aluminum nitride, silicon nitride, and silicon nitride oxide.

5. (original): A semiconductor device according to claim 1, wherein the dielectric film is made of any one of PZT material and bismuth material.

6.-23. (canceled)

24. (currently amended): A semiconductor device comprising:

 a first insulating film formed over a semiconductor substrate;

 a capacitor constructed by forming a lower electrode, a dielectric film, and an upper electrode sequentially over the first insulating film;

 a first capacitor protection insulating film covering the dielectric film and the upper electrode;

 a second capacitor protection insulating film formed on the first capacitor protection insulating film; and

 a second insulating film formed on the second capacitor protection insulating film;

 wherein an amount of carbon contained in the second capacitor protection insulating film is larger than an amount of carbon contained in the second insulating film, and

 the second capacitor protection insulating film covering continuously over the capacitor and the first insulating film,

wherein the second capacitor protection insulating film is a silicon oxide film, and

wherein the second insulating film is a silicon oxide film.